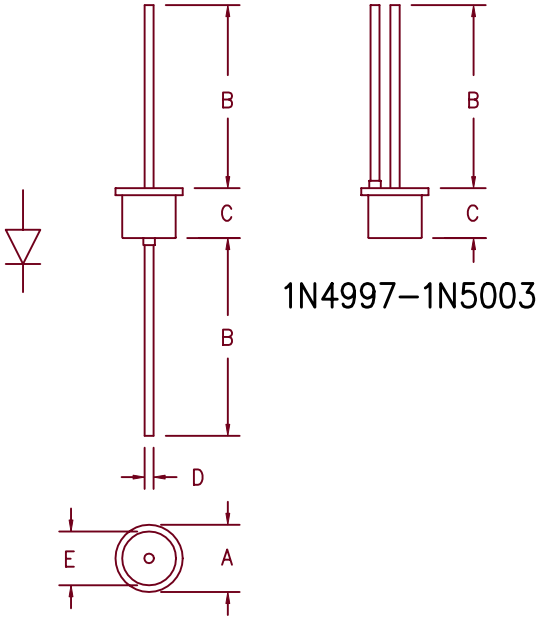
Silicon Rectifiers
1N4719–1N4725,1N4997–1N5003



Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	---	.450	---	11.43	Dia.
B	.980	---	24.89	---	
C	---	.300	---	7.62	
D	.046	.056	1.17	1.42	Dia.
E	---	.350	---	8.89	Dia.

Microsemi Catalog Number	Peak Reverse Voltage
1N4719, 1N4997	50V
1N4720, 1N4998	100V
1N4721, 1N4999	200V
1N4722, 1N5000	400V
1N4723, 1N5001	600V
1N4724, 1N5002	800V
1N4725, 1N5003	1000V

- High Surge Capability
- 175°C Junction Temperature
- V_{RRM} 50 to 1000 Volts
- 3 Amp Current Rating
- Hermetically Sealed

Electrical Characteristics

Average forward current	$I_{F(AV)}$ 3.0 Amps	T_A = 119°C, Square wave, $R_{\theta JL}$ = 12°C/W, L = 1/4"
Maximum surge current	I_{FSM} 300 Amps	8.3ms, half sine, T_J = 175°C
Max peak forward voltage	V_{FM} 1.0 Volts	I_{FM} = 3.0A: T_J = 25°C*
Max peak reverse current	I_{RM} 25 µA	V_{RRM}, T_J = 25°C

*Pulse test: Pulse width 300 µsec, Duty cycle 2%

Thermal and Mechanical Characteristics

Storage temperature range	T_{STG}	−65°C to 175°C
Operating junction temp range	T_J	−65°C to 175°C
Maximum thermal resistance	L = 1/4" $R_{\theta JL}$	12°C/W Junction to Lead
Weight		.08 ounces (2.3 grams) typical

11–13–00 Rev. 1

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Figure 1
Typical Forward Characteristics

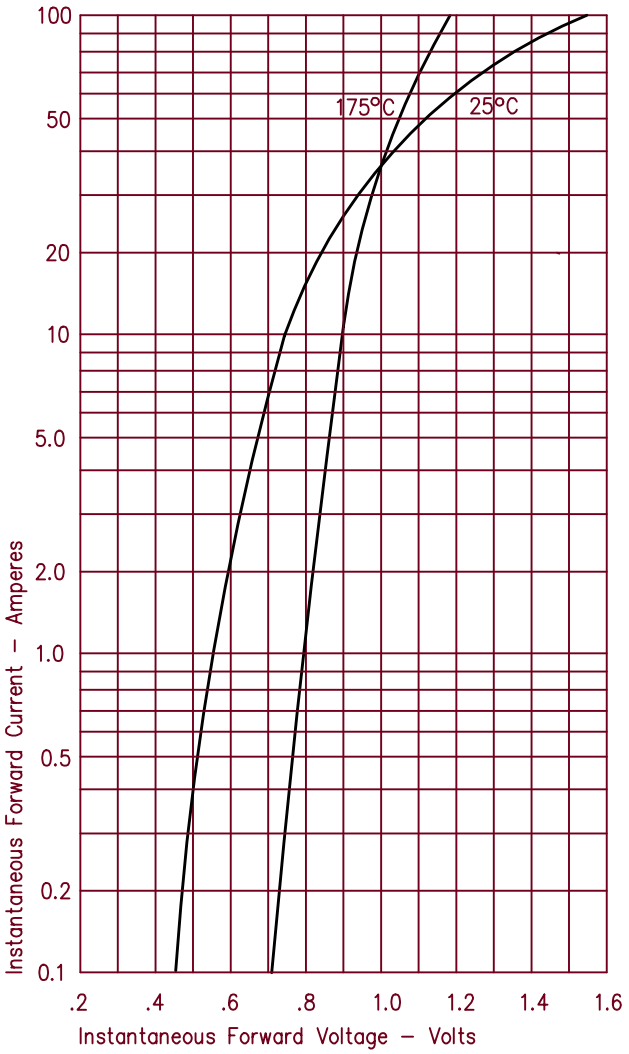

Figure 2
Typical Reverse Characteristics

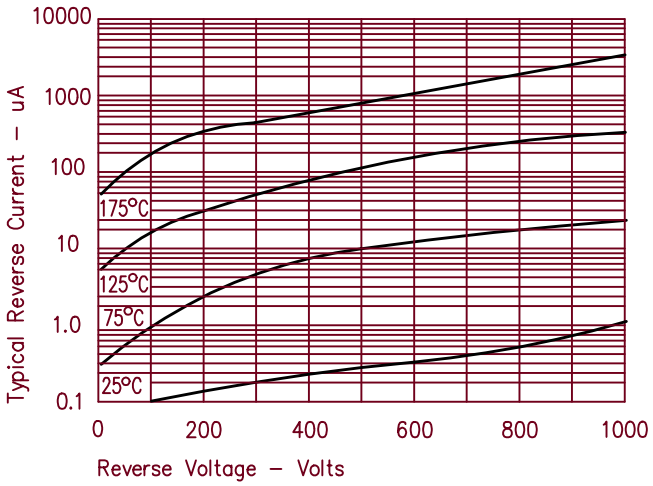

Figure 3
Forward Current Derating